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TOSHIBA

Discrete Semiconductors

1SV257

Variable Capacitance Diode

Silicon Epitaxial Planar Type

VCO For UHF Ratio

Features

- DZSC.CON • Ultra Low Series Resistance : $r_s = 0.2\Omega$ (Typ.)
- Useful for Small Size Set

Absolute Maximum Ratings (Ta = 25°C)									
CHARACTERISTIC	SYMBOL	RATING		UNI					

Reverse Voltage	V _R	15	V
Junc <mark>tion Temperature</mark>	Tj	125	°C
Stora <mark>ge Temperat</mark> ure Range	T _{stg}	-55 ~ 125	°C



Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reve <mark>rse</mark> Voltage	V _R	I _R = 1µA	15	_	-	V
Reverse Current	I _R	V _R = 15V	-	-	3	nA
Capacitance	C2V	$V_{R} = 2V$, f = 1MHz	14	15	16	pF
Capacitance	C10V	V _R = 10V, f = 1MHz	5.5	6	6.5	pF
Capacitance Ratio	C2V/C10V	-	2.0	2.5	-	
Series Resistance	r _s	V _R = 5V, f = 470MHz		0.2	0.4	Ω
网络	F	B3 TD ISC. CON	l.			

DZSC.CO

Marking









 $I_R - V_R$

NOTE : δ_{C} (%) = $\frac{C(Ta) - C(25)}{C(25)} \times 100$

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